

MCMA140P1600TA-NI

Thyristor Module

 $V_{RRM} = 2x \, 1600 \, V$

 $I_{TAV} = 140 A$

 $V_{T} = 1,28 V$

Phase leg

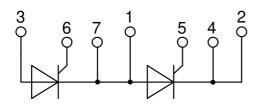
Part number

MCMA140P1600TA-NI



Backside: isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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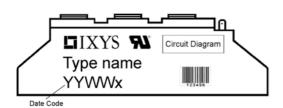
MCMA140P1600TA-NI

Thyristo	r				Ratings	S	ı
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	١
V _{RRM/DRM}	max. repetitive reverse/forward bl	ocking voltage	$T_{VJ} = 25^{\circ}C$			1600	١
R/D	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μA
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 140^{\circ}C$			10	m/
V _T	forward voltage drop	$I_T = 150 A$	$T_{VJ} = 25^{\circ}C$			1,29	١
		$I_{T} = 300 \text{ A}$				1,63	١
		$I_T = 150 A$	$T_{VJ} = 125^{\circ}C$			1,28	١
		$I_{T} = 300 \text{ A}$				1,70	١
I _{TAV}	average forward current	$T_c = 85^{\circ}C$	$T_{VJ} = 140$ °C			140	/
T(RMS)	RMS forward current	180° sine				220	ļ
V _{T0}	threshold voltage	oss calculation only	$T_{VJ} = 140^{\circ}C$			0,85	١
r _T	slope resistance	oss calculation only				2,8	mΩ
R _{thJC}	thermal resistance junction to cas	e				0,22	K/W
R _{thCH}	thermal resistance case to heatsing	nk			0,2		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			520	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			2,40	k/
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			2,59	k/
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			2,04	k/
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			2,21	k/
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			28,8	kA ² s
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			27,9	kA2s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			20,8	kA ² s
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			20,2	kA2s
C,	junction capacitance	V _R = 400V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		119		рF
P_{GM}	max. gate power dissipation	t _P = 30 μs	T _C = 140°C			10	V
	,	t _P = 300 μs				5	W
P_{GAV}	average gate power dissipation					0,5	W
(di/dt) _{cr}	critical rate of rise of current	T _{v,i} = 140°C; f = 50 Hz	repetitive, $I_T = 450 A$			150	A/μs
701		$t_P = 200 \mu s; di_G/dt = 0.45 A/\mu$	•				
		$I_{G} = 0.45A; V_{D} = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 150 \text{ A}$			500	A/μs
(dv/dt) _{cr}	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DBM}$	T _{v.i} = 140°C			1000	
() (-	v	R _{GK} = ∞; method 1 (linear v	••				
V _{GT}	gate trigger voltage	$V_D = 6 \text{ V}$	$T_{VJ} = 25^{\circ}C$			1,5	V
- 61	0 00 0		$T_{VJ} = -40^{\circ}C$			1,6	١
I _{GT}	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 25^{\circ}C$			150	m/
-G1	gant mggt ramen	• ₀ = • •	$T_{VJ} = -40^{\circ}C$			200	m/
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DBM}$	$T_{VJ} = 140^{\circ}C$			0,2	I
I _{GD}	gate non-trigger current	- D / S - DRM	. 73			10	m/
I _L	latching current	t _p = 10 μs	$T_{VJ} = 25^{\circ}C$			200	m/
·L	atoming outfort	$I_p = 10 \mu\text{s}$ $I_G = 0.45 \text{A}; \text{di}_G/\text{dt} = 0.45 \text{A}$				200	111/-
1	holding current	$V_{D} = 6 \text{ V } R_{GK} = \infty$	T _{vJ} = 25°C			200	m <i>P</i>
I _H							Ì
t _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25^{\circ}C$			2	μ
	turn-off time	$I_G = 0.45 \text{A}; \text{ di}_G/\text{dt} = 0.45 \text{A}$ $V_R = 100 \text{ V}; I_T = 150 \text{A}; V_D$			405		i !
tq	uurn-on time	V = 100 V· I = 150Δ·V	⁄2 V I125 °C	l	185	l	με



MCMA140P1600TA-NI

Package TO-240AA				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{VJ}	virtual junction temperatur	е			-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2,5		4	Nm
$\mathbf{M}_{_{\mathbf{T}}}$	terminal torque				2,5		4	Nm
d _{Spp/App}	croopago distanco on surf	ace striking distance through air	terminal to terminal	13,0	9,7			mm
$d_{\text{Spb/Apb}}$	creepage distance on sun	ace Striking distance through an	terminal to backside	16,0	16,0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		4800			٧
		t = 1 minute			4000			٧



Part description

M = Module

C = Thyristor (SCR) M = Thyristor

A = (up to 1800V) 140 = Current Rating [A]

P = Phase leg

1600 = Reverse Voltage [V]

TA = TO-240AA-1B - = Hyphen

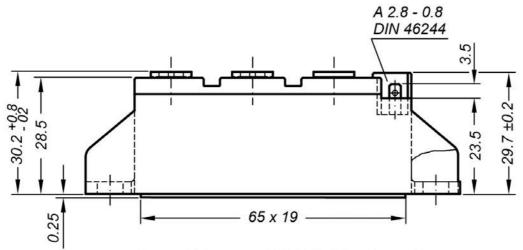
NI = without metal inserts

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA140P1600TA-NI	MCMA140P1600TA-NI	Box	36	

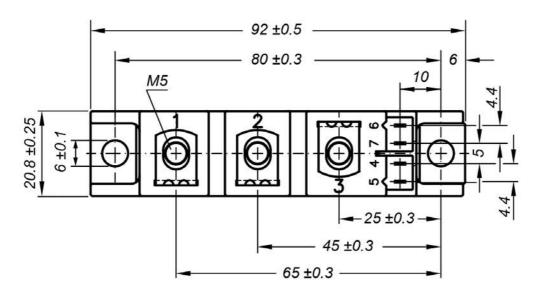
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 140$ °C
$I \rightarrow V_0$)— <u>R</u> o	Thyristor		
V _{0 max}	threshold voltage	0,85		V
$R_{0 max}$	slope resistance *	1,6		$m\Omega$



Outlines TO-240AA



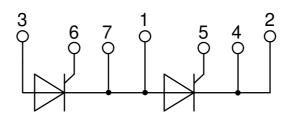
General tolerance: DIN ISO 2768 class "c"



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 200L (L = Left for pin pair 4/5)
Type ZY 200R (R = Right for pin pair 6/7) UL 758, style 3751







Thyristor

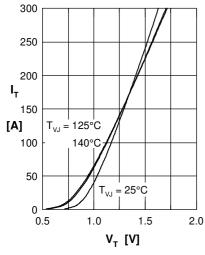


Fig. 1 Forward characteristics

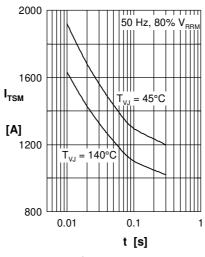


Fig. 2 Surge overload current I_{TSM} : crest value, t: duration

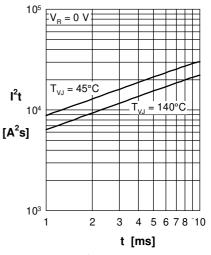


Fig. 3 I^2 t versus time (1-10 s)

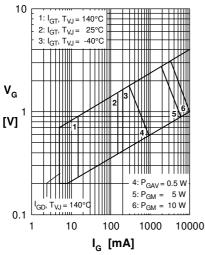


Fig. 4 Gate voltage & gate current

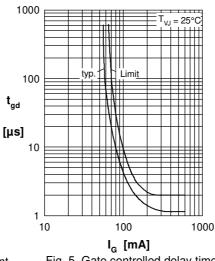


Fig. 5 Gate controlled delay time t_{ad}

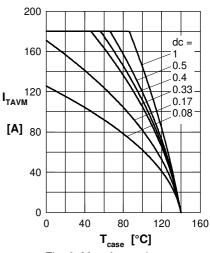


Fig. 6 Max. forward current at case temperature

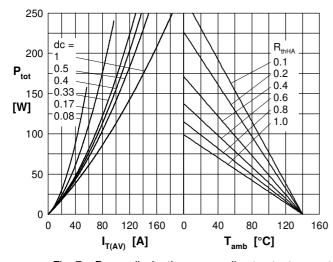


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

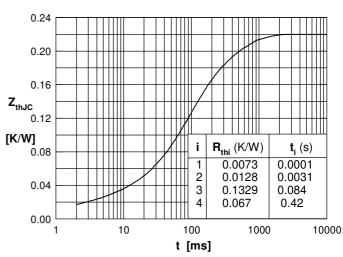


Fig. 8 Transient thermal impedance junction to case